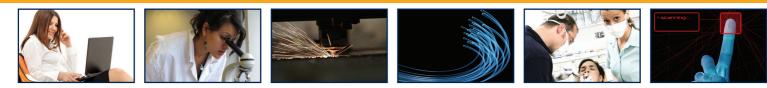
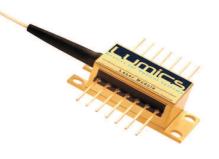
_UMICS Member of scansonic Group



LU1550M150 1550nm Laser Module, Seed Laser c.w. or pulsed mode



Description:

The Lumics LU1550M150 laser diode module contains an optimized InP substrate based quantum well high power laser diode. It has been designed for customer specific applications and is available with special FBG's and fibers. The qualification contains a set of optoelectronic, thermal and mechanical tests. Each laser diode module is individually serialized for traceability and is shipped with a specified set of test data.

Features & Functions:

- Wavelength 1550nm
- Up to 150mW c.w. operating power
- Up to 200mW peak power
- Short pulses 5nsec 500nsec

Options:



 Low inductive rise fall time <1 ns

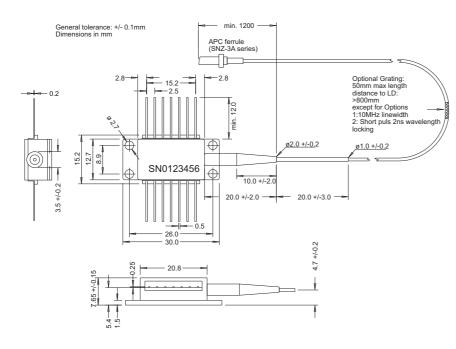
Benefits:

- All laser welded
- High reliability

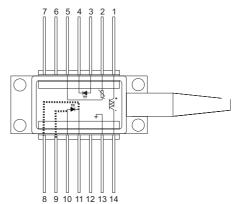
Applications:

Sensor applications

Module Drawing (dimensions in mm)



Pin Connections



Pin	Function	Pin	Function
1	Cooler (+)	8	(*) LD Cathode (-)
2	Thermistor	9	(*) LD Anode (+)
3	nc	10	LD Anode (+)
4	nc	11	LD Cathode (-)
5	Thermistor	12	nc
6	nc	13	Case ground
7	nc	14	Cooler (-)

(*) Optional low inductive

We manufacture diode lasers.

Electrical and Optical Characteristics (at 25°C (T_{chip} and T_{case}) and Begin of Life (BOL)):

	Conditions					
Operating power	C.W.	Pop		150		mW
Operating current	C.W.	l _{op}		600	800	mA
Pulsed operating peak power	< 500ns / duty cycle <5%	Pop_puls		200		mW
Pulsed operating peak current	< 500ns / duty cycle <5%	I _{op_puls}			1	Α
Rise and fall time (4)					2	nsec
Threshold current		l _{th}		50		mA
Forward voltage	at I _{op}	V _{op}		1.6		V
Peak wavelength $\lambda_{\text{peak}}(2)$	at Pop without FBG	λ	1540	1550	1560	nm
Spectral Width (FW90% energy inclusion) (2	$\Delta \lambda$		6		nm	
Spectral Width (FWHM) (3)	at P _{op} with FBG	$\Delta \lambda$		0.8		nm
Peak Wavelength at λ_{peak} (3)	at P _{op} with FBG	λ	1548	1550	1552	nm
Spectral shift with internal temp.	without FBG, internal Tchip	Δ / T		0.6		nm/ °C
Spectral shift with temp.	with FBG Temp	Δ/Τ		0.01	0.02	nm/ °C
Side mode suppression (2)	at Pop, with FBG			20		dB
TEC current	chip 25°C, case 70°C	I _{TEC}		1.4		Α
TEC voltage	chip 25°C, case 70°C	V _{TEC}		2.2		V
Thermistor resistance	T=25°C	Rth	9.5	10	10.5	kOhm
Thermistor B constant		В	3850	3950	4050	K
Steinhart-Hart-Equation coefficients	C ₁ = 1.1292E-03 / C ₂ = 2.3411E-04 / C ₃ = 8.7755E-08					
Large signal modulation bandwidth				200		MHz
Fiber Specifications						
Fiber type	single mode (SMF28, NA 0.13)					

Notes:

Ensure sufficient protection against high energy back reflection pulses from solid state lasers. High energy back reflection damages the diode (for 1) example stimulated Brillouin scattering). Typical damage threshold for 8ns puls @200KHz is 0.05µJ (this level is not covered under warranty).

2) Intensity noise of light from modules with PM fiber after polarizer increases with lower polarization extinction ratio (example 6 /10/13 dB can result in intensity noise as high as 50/20/5 %). The intensity noise is sensitive to varying stress (by mechanical and temperature effects) introduced to the PM fiber

Wavelength is measured in air. Without wavelength stabilisation by a fiber bragg grating (FBG) multiple peaks (side modes) around the average wavelength 3) for a specific current in a range of (1-3) nm are observed. The full width half maximum (FWHM) of those peaks can suddenly narrow or broaden. Side mode suppression counts the first side peaks next to the main peak. A peak is defined by significant lower values left and right to this peak

4) With wavelength stabilisation by a fiber bragg grating (FBG) a single peak for a specific current is observed. The full width half maximum (FWHM) of this single peaks is stable over time as long as it it is not disturbed by further back reflection from the outgoing optical path.

5) Rise and fall depends on appropriate driver and can be lower than 1ns with the low inductive version.

Absolute Maximum Ratings

Parameter	Symbol	Min	Мах	
Storage temp.	T _{max}	-40	85	°C
Operating case temp.	T _{op, case}	-20	70	°C
Operating chip temp.	T _{op, chip}	20	40	°C
Soldering temp. (max. 10sec)		260		°C
LD Forward current (c.w.)	I _{op max}		0.85	А
LD Forward current (Pulse 500ns 5	1	А		
LD Reverse voltage	V _{R, max}		2	V
TEC Current	I _{TEC}		1.8	А
TEC Voltage	V _{TEC}		3.2	V
ESD Damage (1)			500	V
Fiber pigtail bend radius	SMF28		25	mm
Maximum transient (<3µs) forward c	1.5	А		

(1) A standard human body model (1.5kOhm, 1000pF) is used for ESD thresholds

Note: Absolute maximum ratings may be applied to the laser module for short periode of time only. Exposure to maximum ratings for extended period of time or exposure above one or more max ratings may cause damage or affect the reliability of the device.

User Safety





We manufacture diode lasers.

P_o= 0.5W λ = 1520-1570n